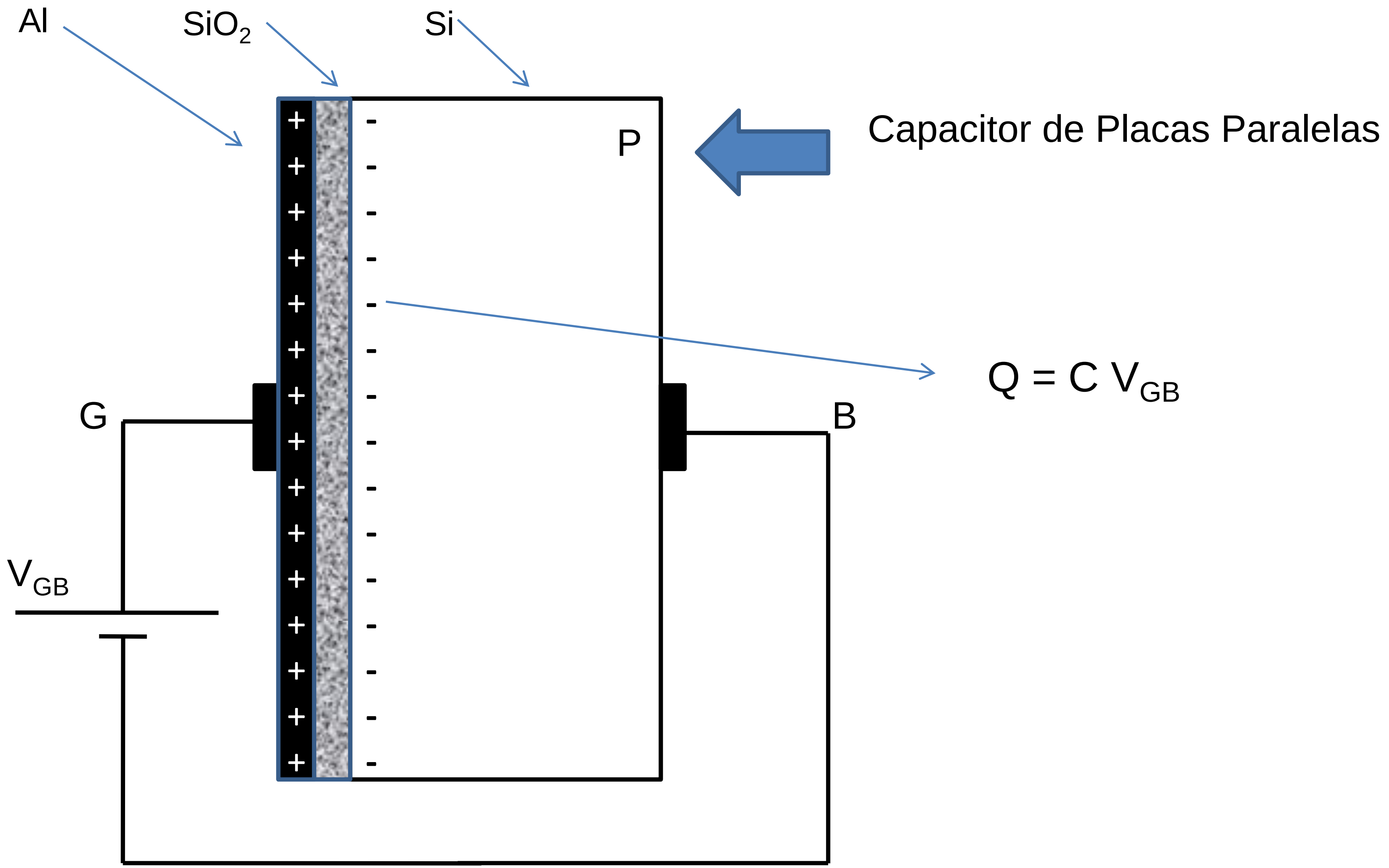
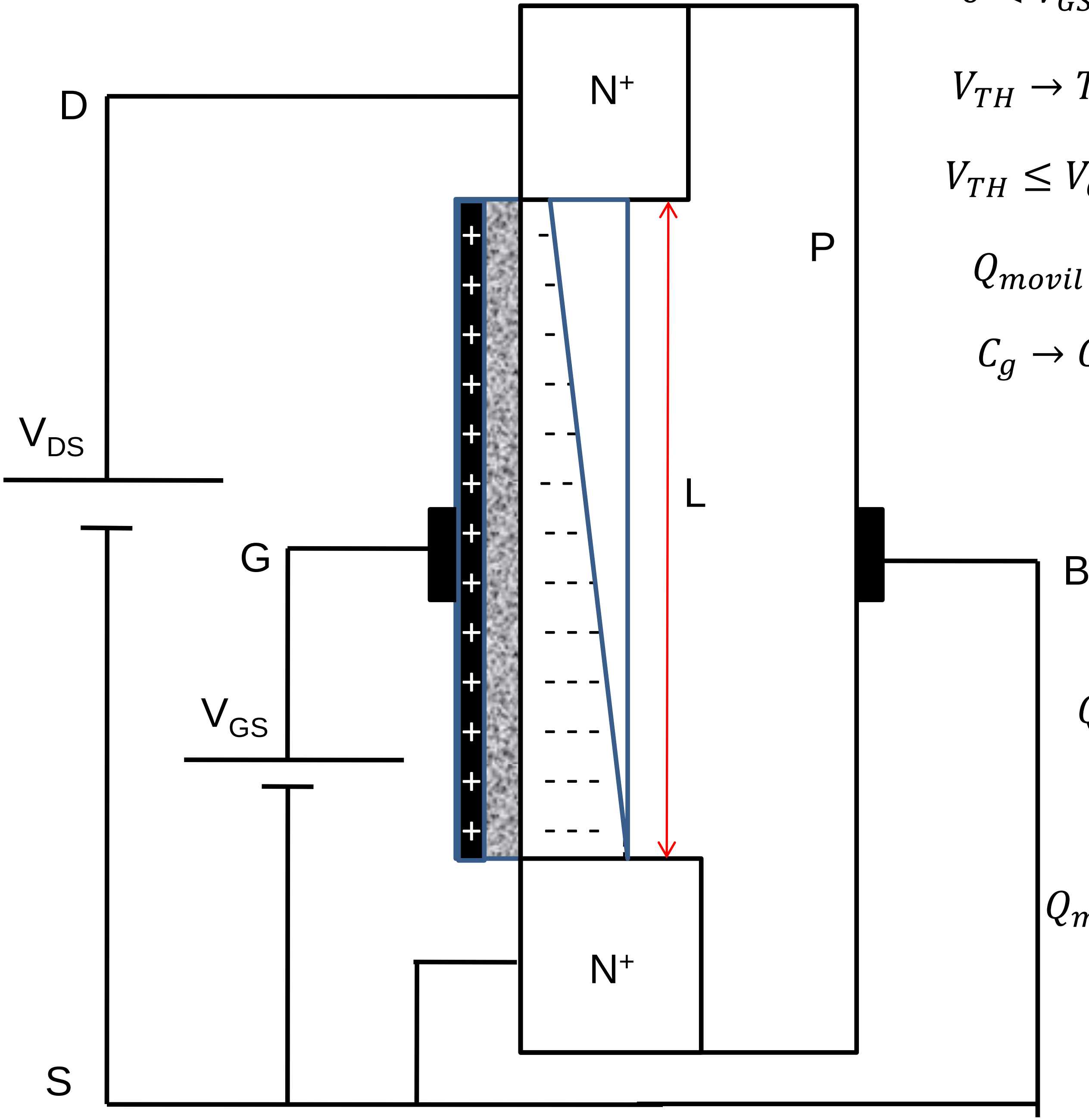
TRANSISTOR DE EFECTO DE CAMPO (FET)

METAL–OXIDO–SEMICONDUCTOR (MOSFET)





$$0 < V_{GS} < V_{TH} \rightarrow Q_{movil} = 0$$

$$V_{TH} \rightarrow Tension\ umbral$$

$$V_{TH} \leq V_{GS} \rightarrow Carga\ movil\ en\ el\ canal$$

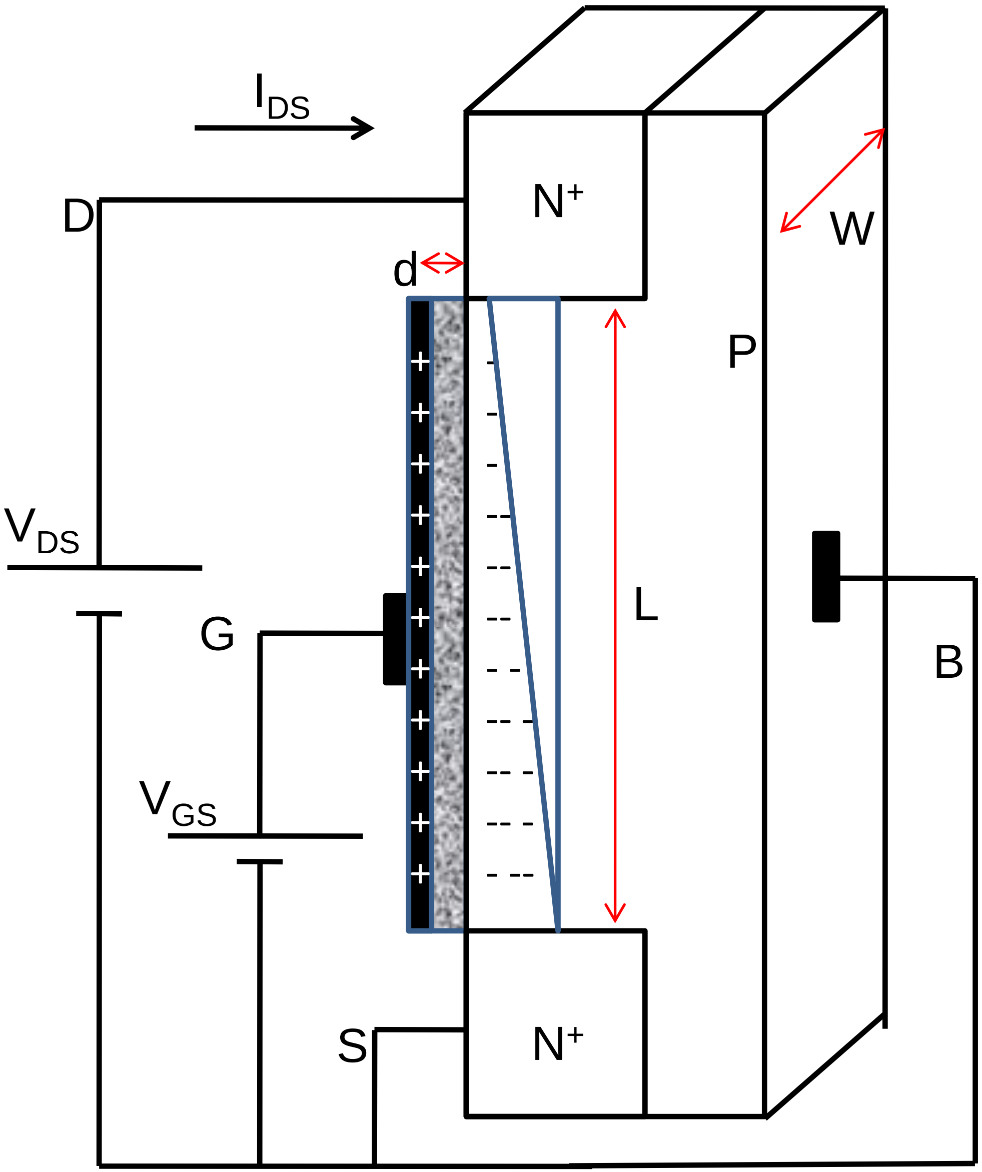
$$Q_{movil} = C_g(V_{GS} - V_{TH})$$

$$C_g \rightarrow Capacidad\ de\ compuerta$$

$$C_g = \varepsilon \frac{A}{d} = \varepsilon \frac{W\ L}{d}$$

$$Q_{movil} = C_g\left(V_{GS} - V_{TH} - \frac{V_{DS}}{2}\right)$$

$$Q_{movil} = \varepsilon \frac{WL}{d}\left(V_{GS} - V_{TH} - \frac{V_{DS}}{2}\right)$$



$$I_{DS} = \frac{Carga\ movil\ en\ el\ canal}{Tiempo\ de\ Transito}$$

$$I_{DS} = \frac{Q_{movil}}{T_T}$$

$$Q_{movil} = \varepsilon \frac{WL}{d}\left(V_{GS} - V_{TH} - \frac{V_{DS}}{2}\right)$$

$$T_T = \frac{L}{v_d} \qquad v_d = \mu E \qquad E = \frac{V_{DS}}{L}$$

$$T_T = \frac{L^2}{\mu V_{DS}}$$

$$I_{DS} = \frac{\mu\varepsilon}{d}\frac{W}{L}\left(V_{GS} - V_{TH} - \frac{V_{DS}}{2}\right)V_{DS}$$

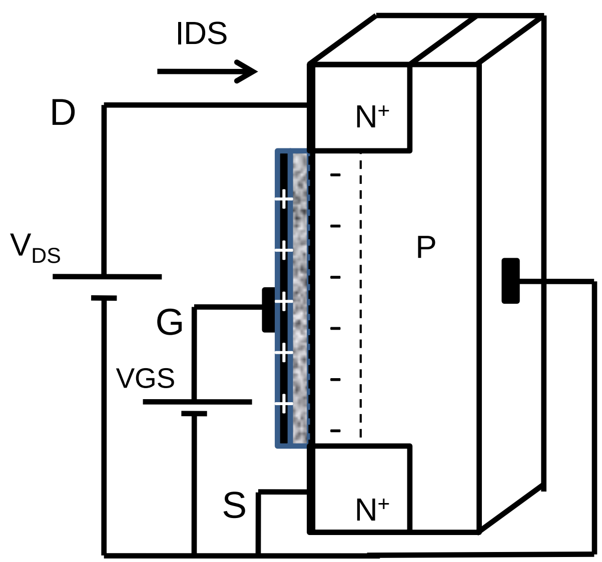
$$\frac{\mu\varepsilon}{d}\frac{W}{L} \rightarrow Depende\ de\ la\ fabricacion$$

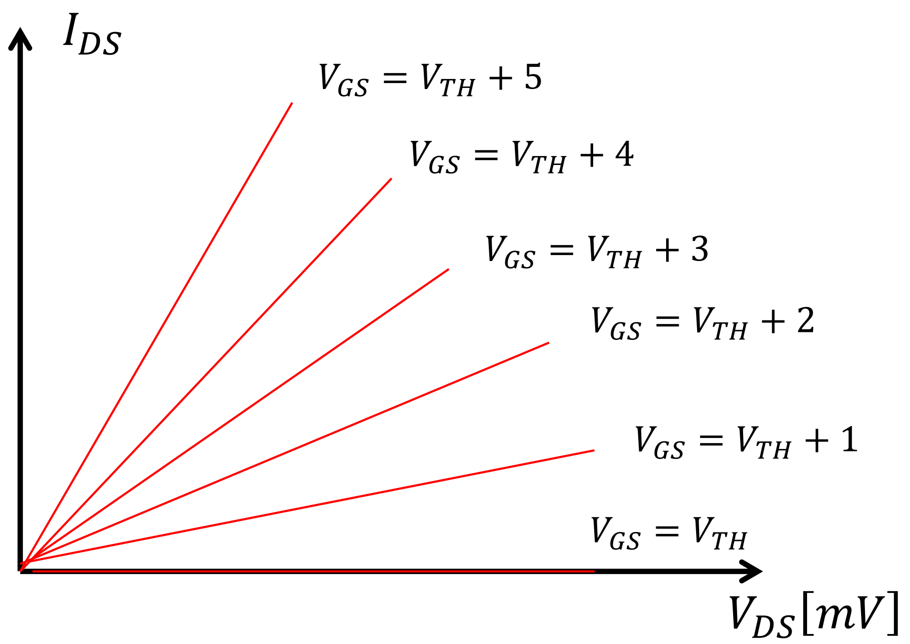
$$\beta = \frac{\mu\varepsilon}{d}\frac{W}{L}$$

$$I_{DS} = \beta(V_{GS} - V_{TH})V_{DS} - \frac{\beta}{2}V_{DS}^2$$

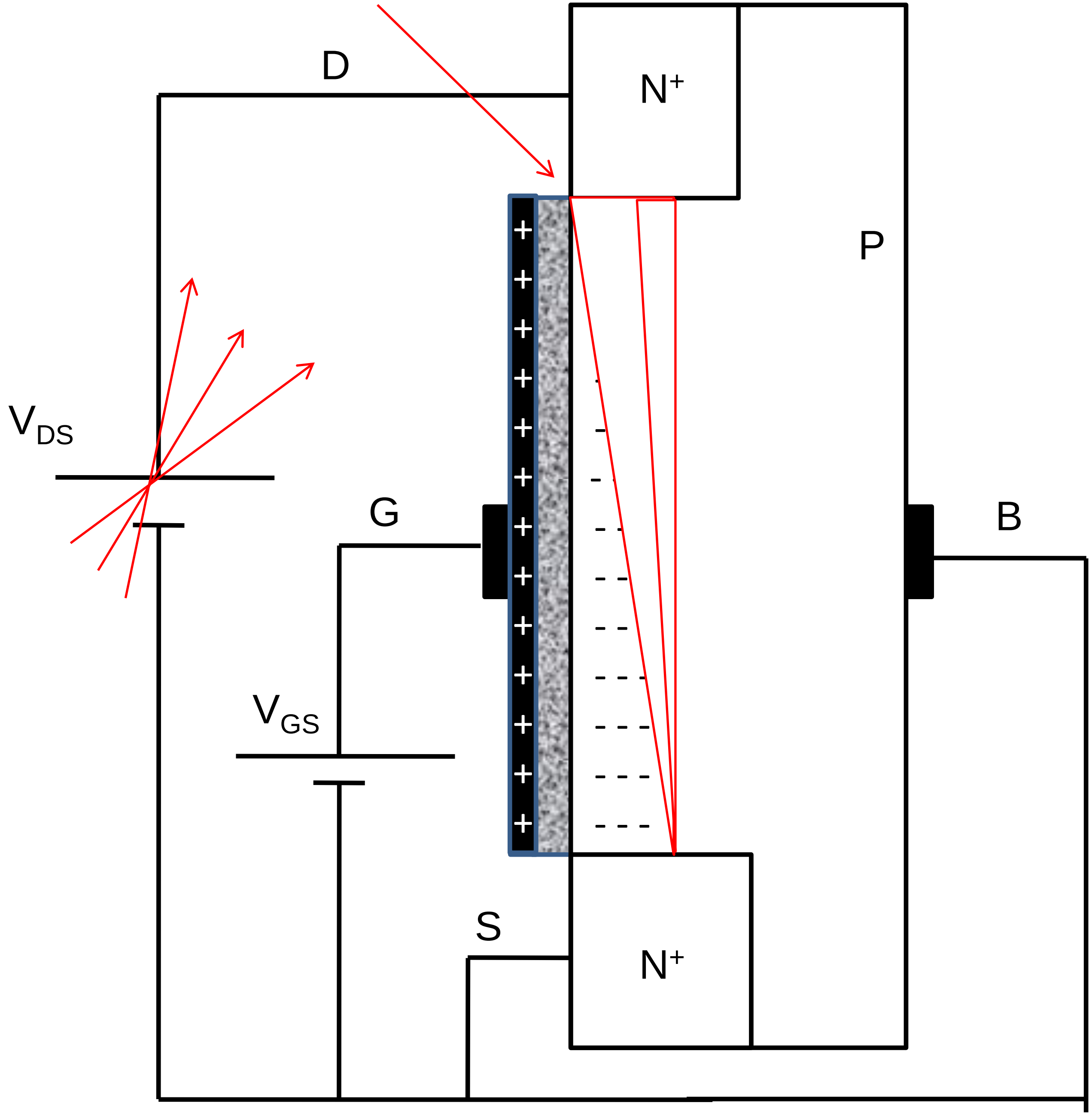
Para V_{DS} bajo → $I_{DS} \approx \beta(V_{GS} - V_{TH})V_{DS}$

El dispositivo entre drenador y fuente se comporta como un resistor cuyo valor es controlado por V_{GS} → $R_{DS} = \frac{V_{DS}}{I_{DS}} = \frac{1}{\beta(V_{GS} - V_{TH})}$





$V_{GS} - V_{DS} = V_{TH}$ → No hay portadores

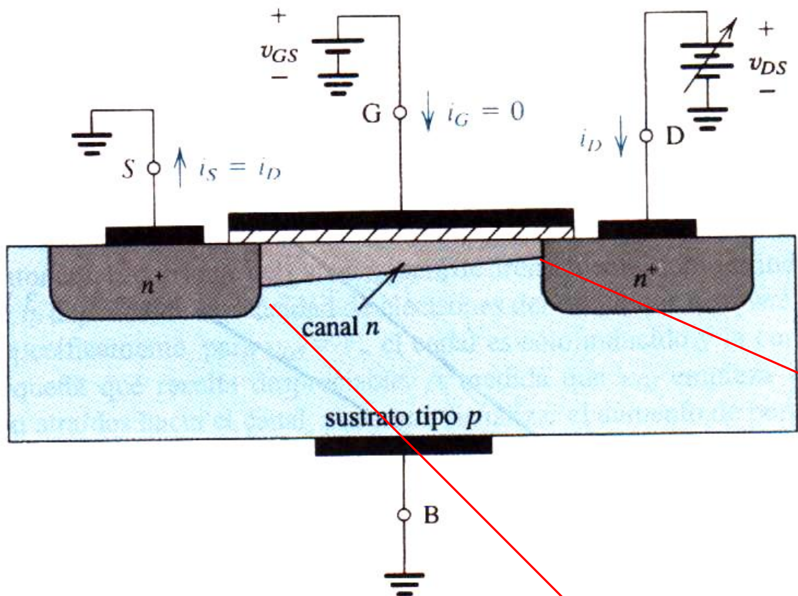


SATURACION

I_{DS} = cte. y no depende de V_{DS}

$$I_{DS} = \frac{\beta}{2}(V_{GS} - V_{TH})^2$$

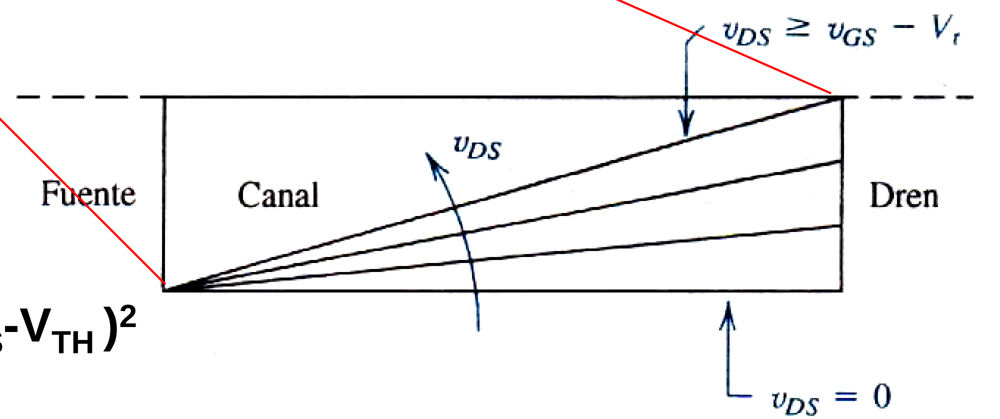
SATURACION



$$I_{DS} = \beta\,(V_{GS}-V_{TH})\,V_{DS} - \frac{\beta}{2}V^2_{DS}$$

$$(V_{GS} - V_{DS}) < V_{TH}$$

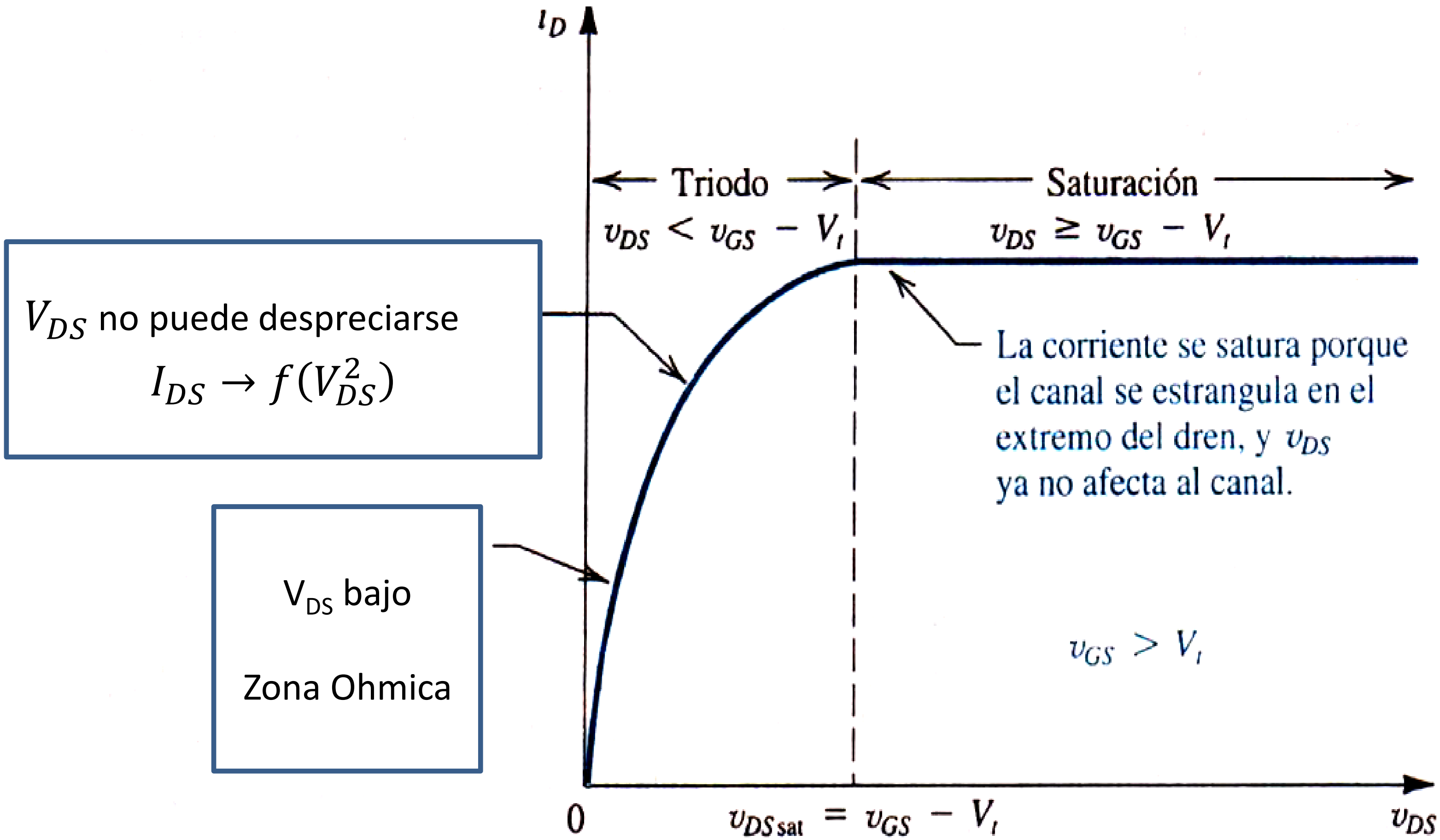
$$V_{DS} = (V_{GS} - V_{TH})$$



$$I_{DS} = \beta\,(V_{GS}-V_{TH})\,(V_{GS}-V_{TH}) - \frac{\beta}{2}(V_{GS}-V_{TH})^2$$

$$I_{DS} = \frac{\beta}{2}(V_{GS}-V_{TH})^2$$

$$I_{DS} = \beta(V_{GS} - V_{TH})V_{DS} - \frac{\beta}{2}V_{DS}^2$$



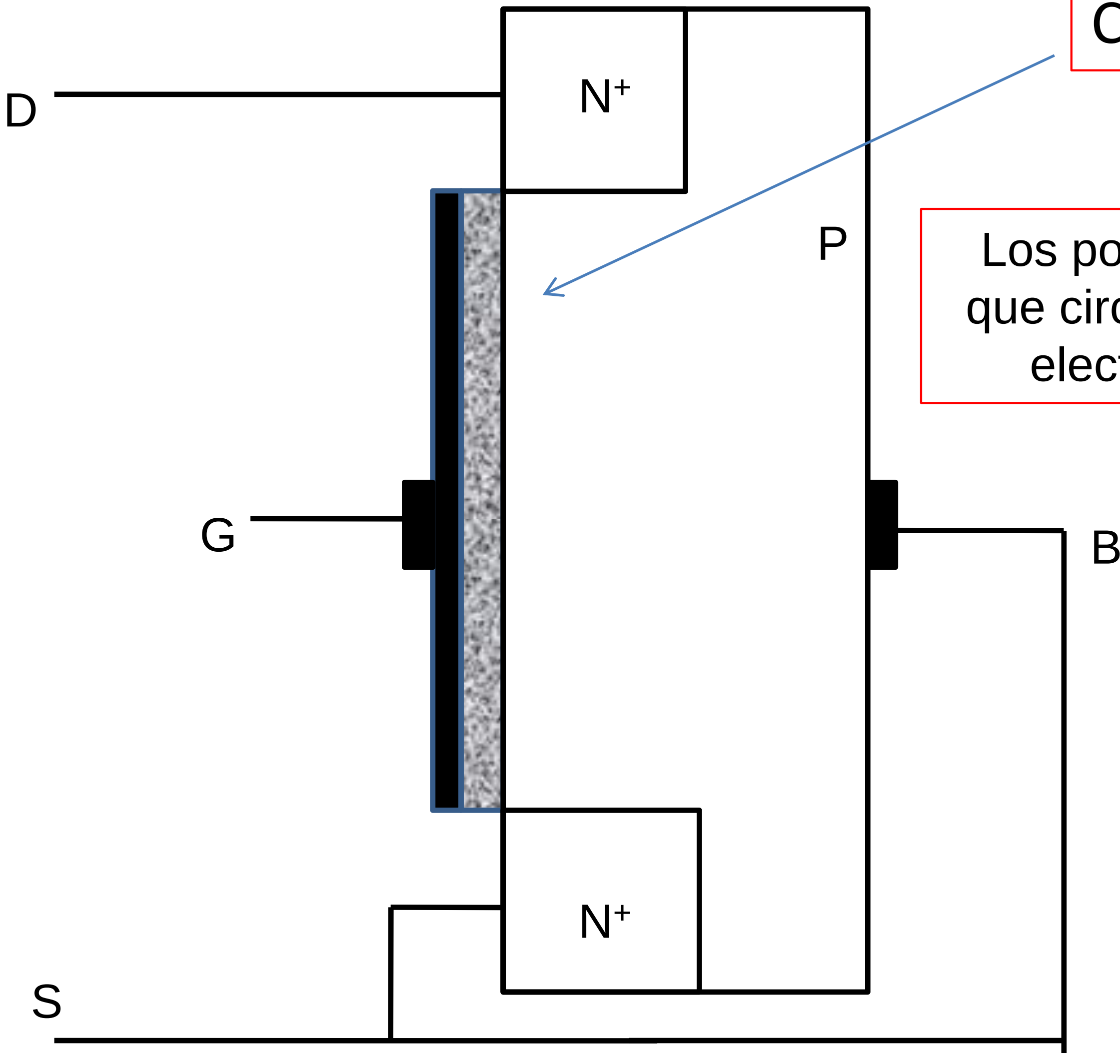
ZONAS DE OPERACION

Corte → $V_{GS} < V_{TH}$ → $I_{DS} = 0$

Ohmica → $V_{GS} \geq V_{TH}$; $V_{GS} - V_{DS} \geq V_{TH}$ → $I_{DS} = \beta(V_{GS} - V_{TH})V_{DS} - \frac{\beta}{2}V_{DS}^2$

Saturación → $V_{GS} \geq V_{TH}$; $V_{GS} - V_{DS} \leq V_{TH}$ → $I_{DS} = \frac{\beta}{2}(V_{GS} - V_{TH})^2$

MOS FET Canal N
Enriquecimiento

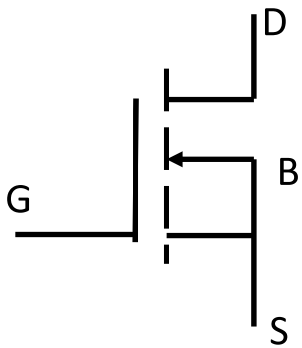


Canal N → Los portadores que circulan son electrones

Enriquecimiento → Sin tension V_{GS} no hay canal

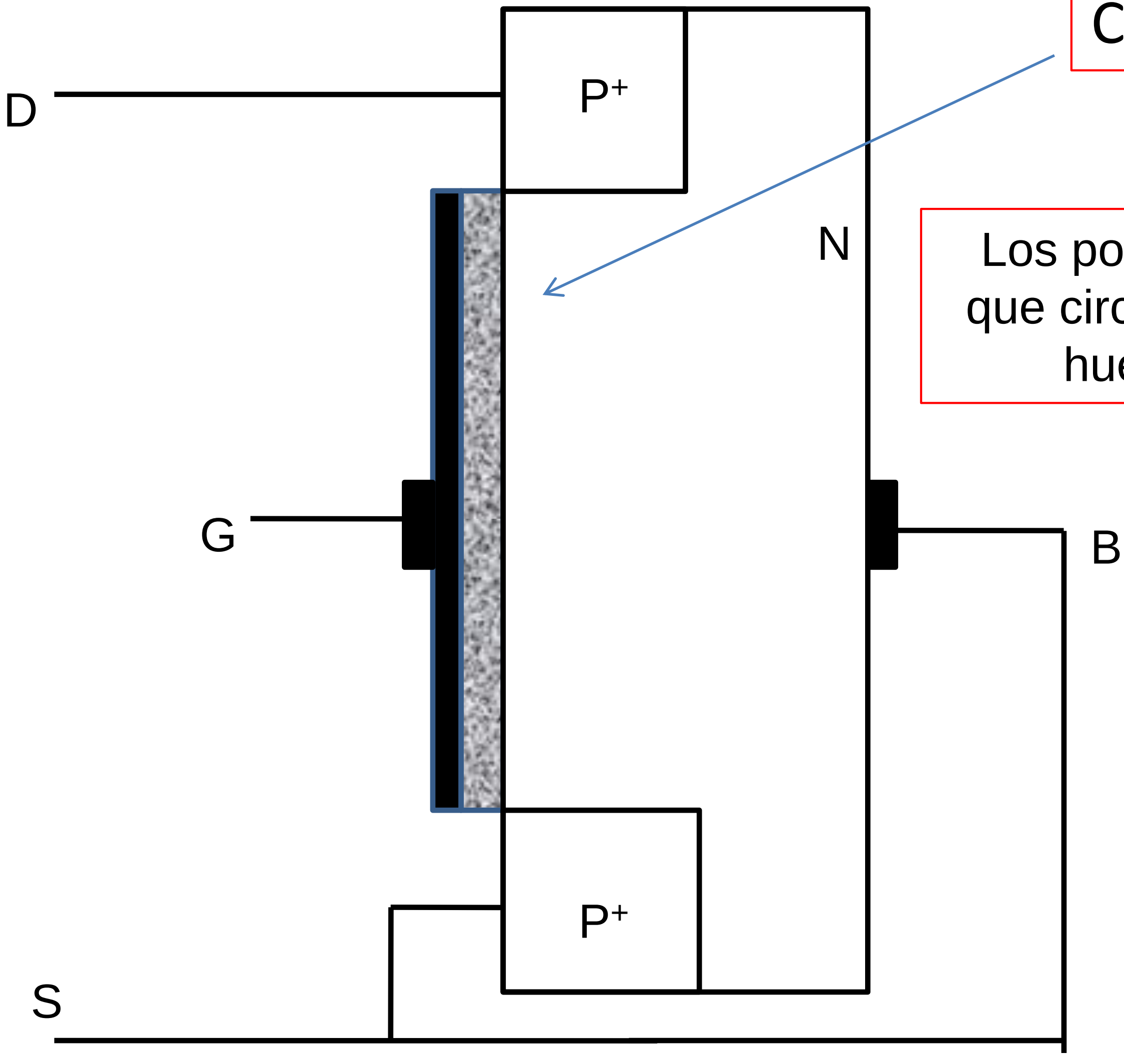
$V_{GS} \geq 0$

$V_{DS} \geq 0$



Símbolo

MOS FET Canal P
Enriquecimiento

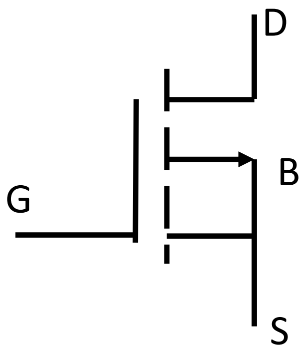


Canal P → Los portadores que circulan son huecos

Enriquecimiento → Sin tensión V_{GS} no hay canal

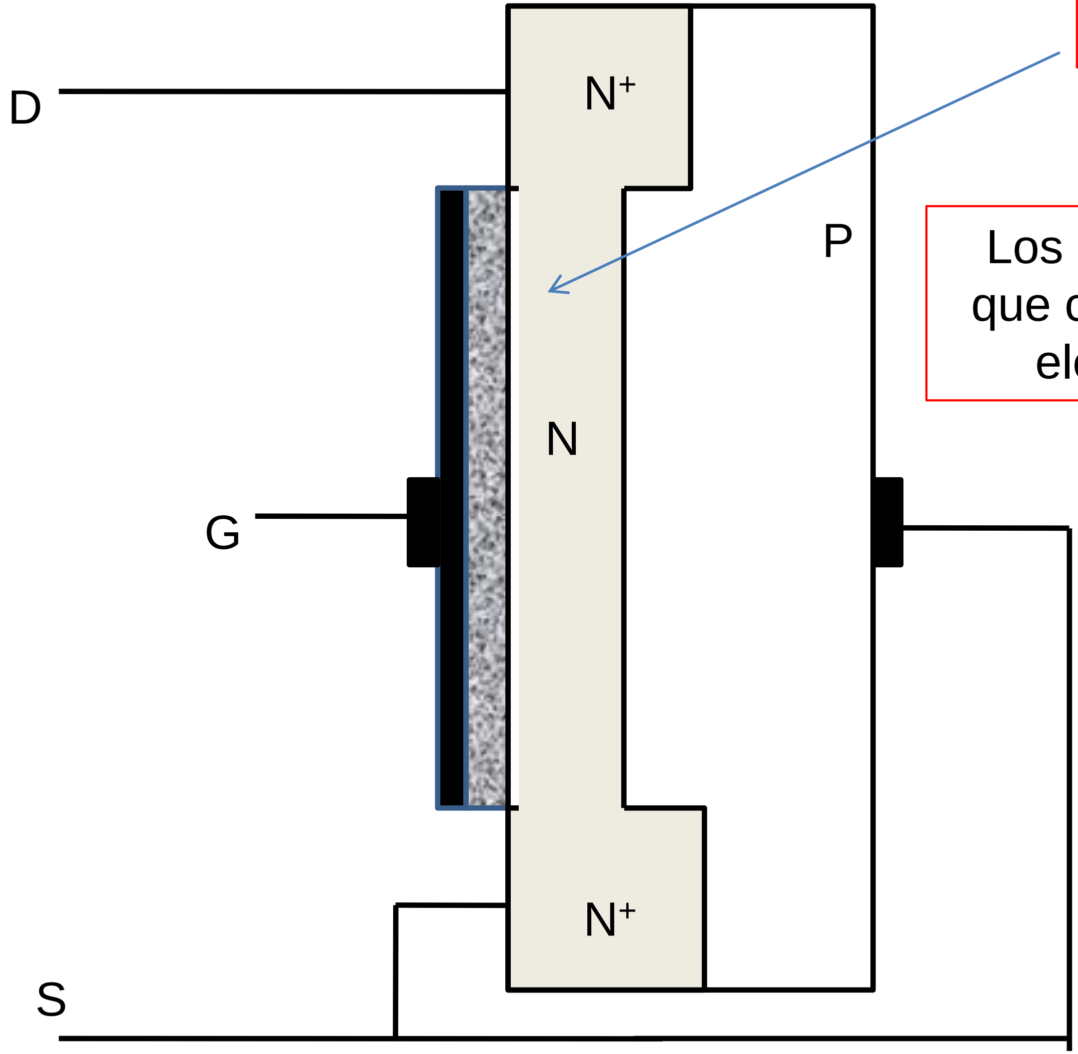
$V_{GS} \leq 0$

$V_{DS} \leq 0$



Símbolo

MOS FET Canal N
Deplexion

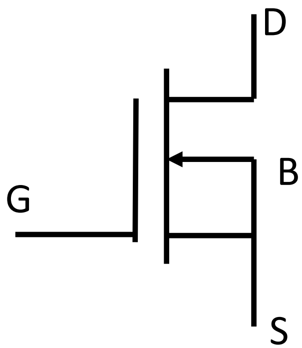


Canal N → Los portadores que circulan son electrones

Deplexion → Sin tension V_{GS} hay canal

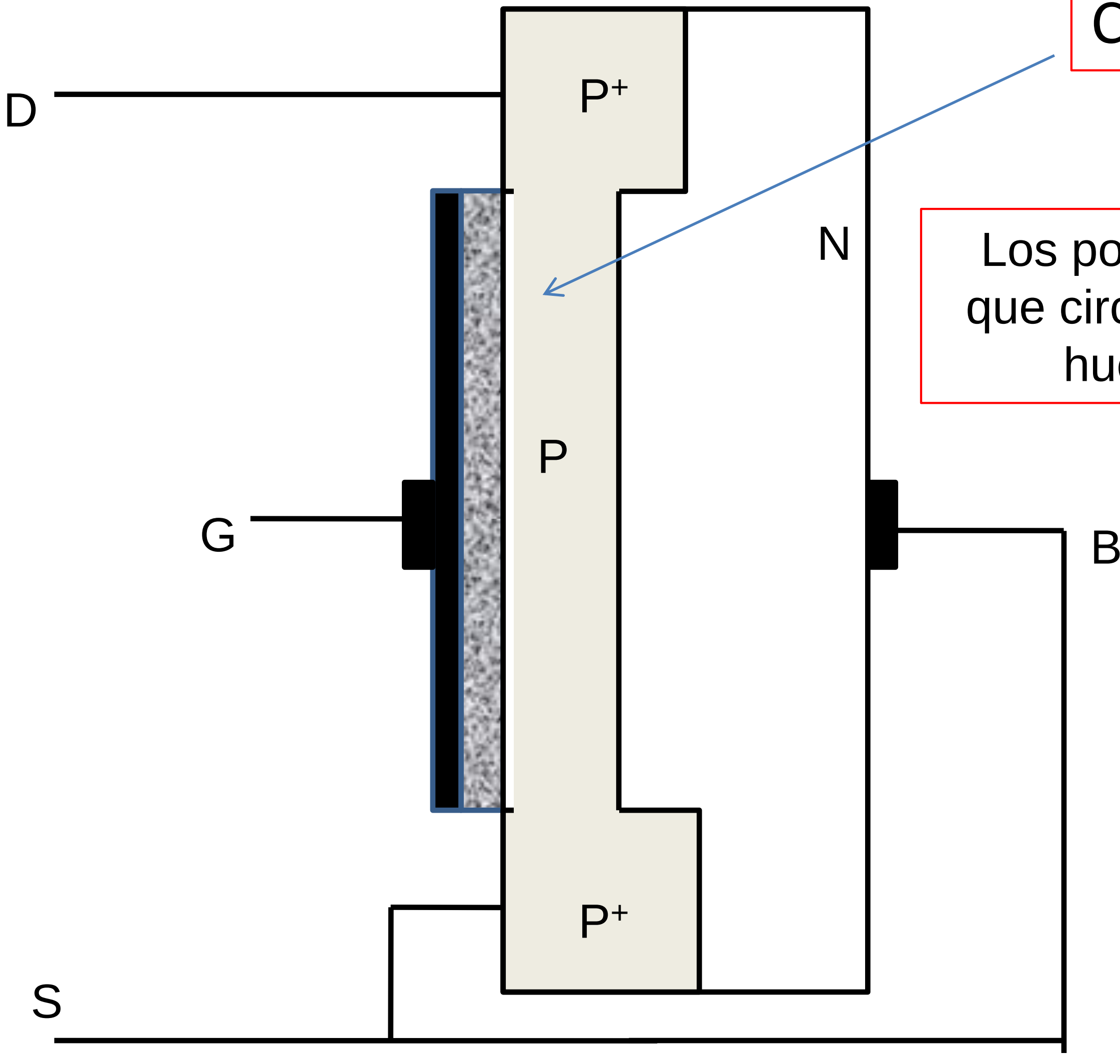
$V_{GS} \lesseqgtr 0$

$V_{DS} \geq 0$



Símbolo

MOS FET Canal P
Deplexion



Canal P

↓

Los portadores que circulan son huecos

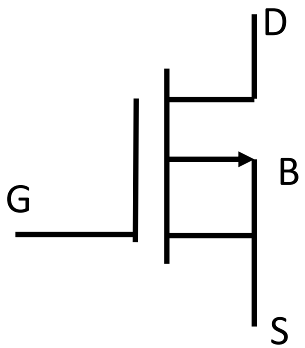
Deplexion

↓

Sin tension V_{GS} hay canal

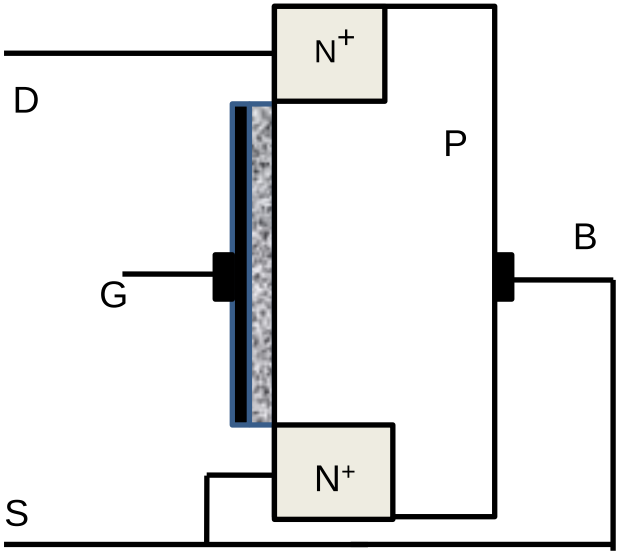
$V_{GS} \lesseqgtr 0$

$V_{DS} \leq 0$

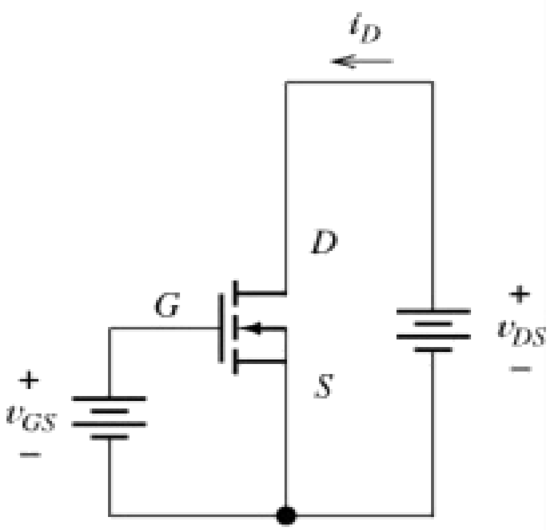


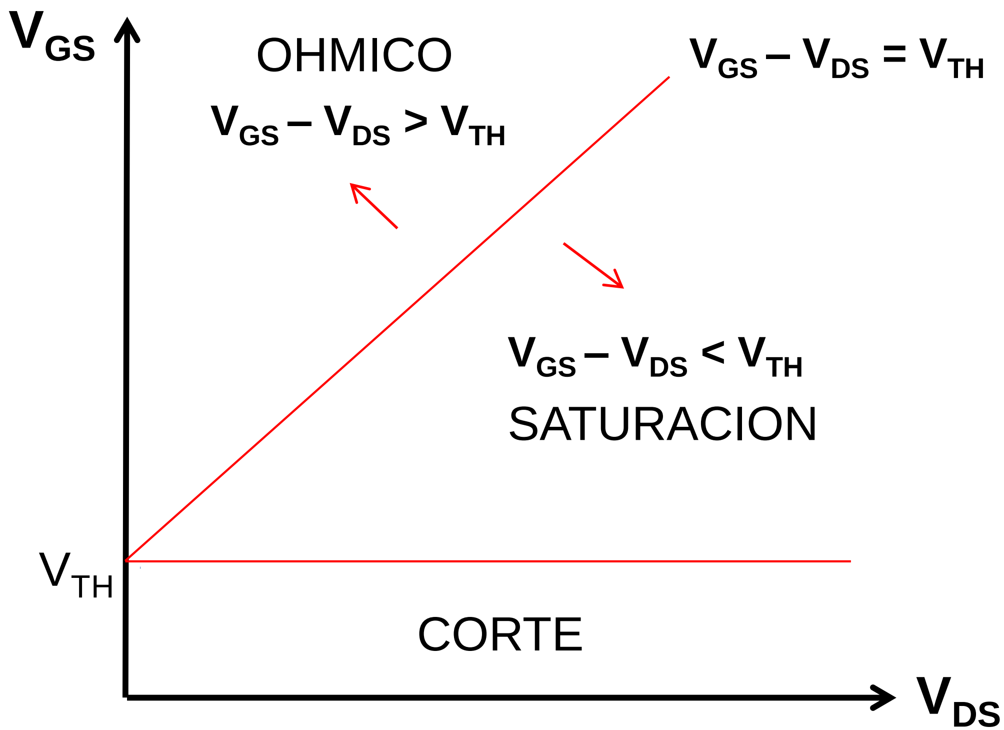
Símbolo

MOS FET Canal N Enriquecimiento

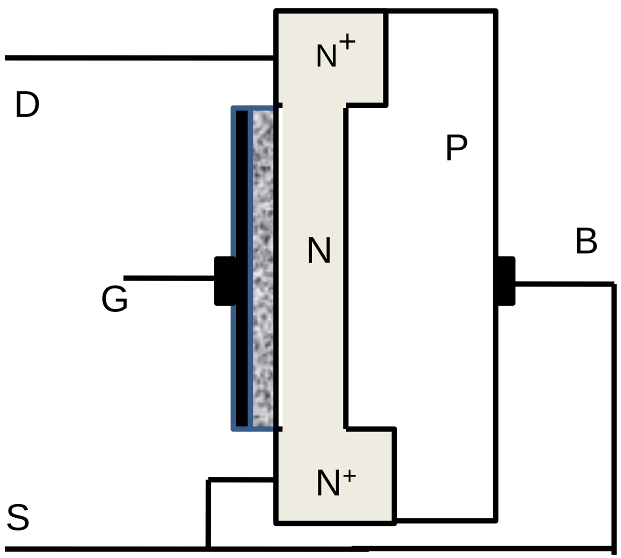


VGS vs VDS

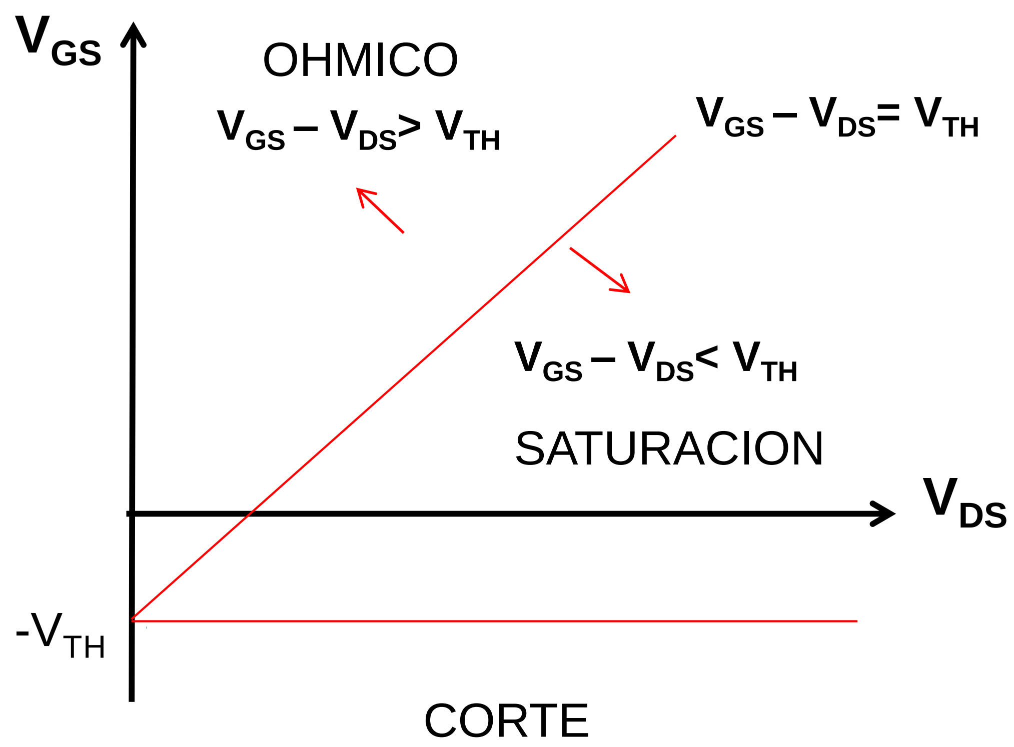


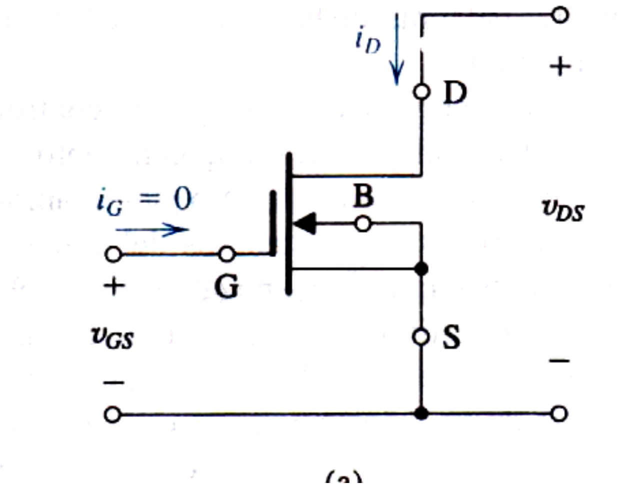


MOS FET Canal N Deplexion

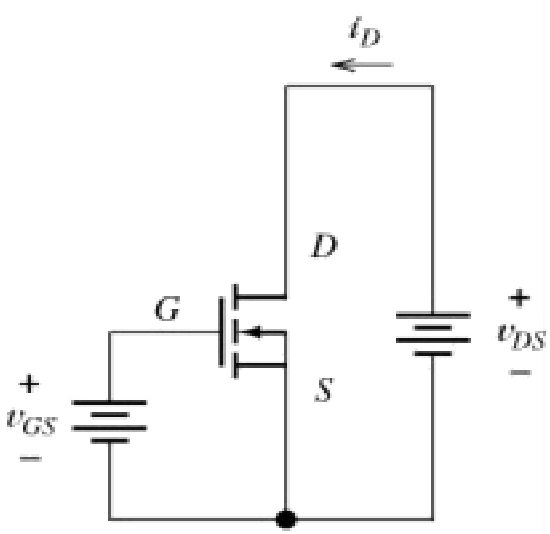


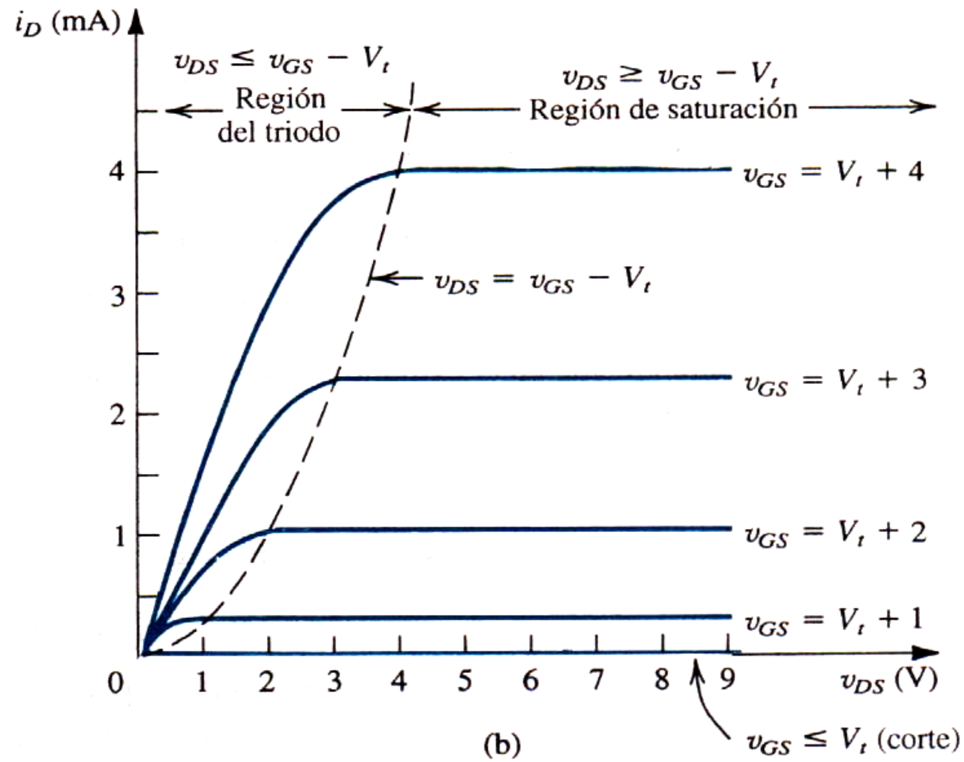
VGS vs VDS



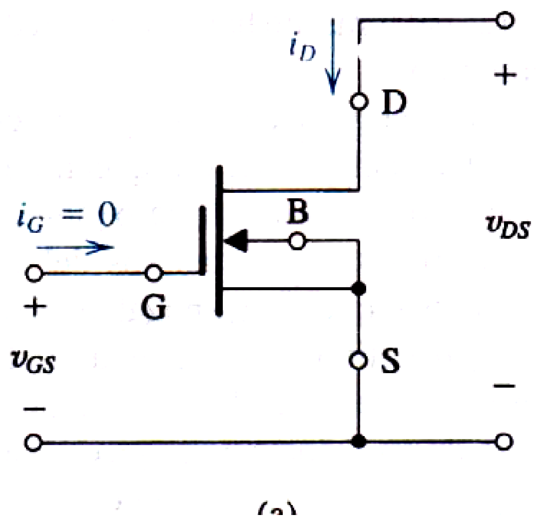


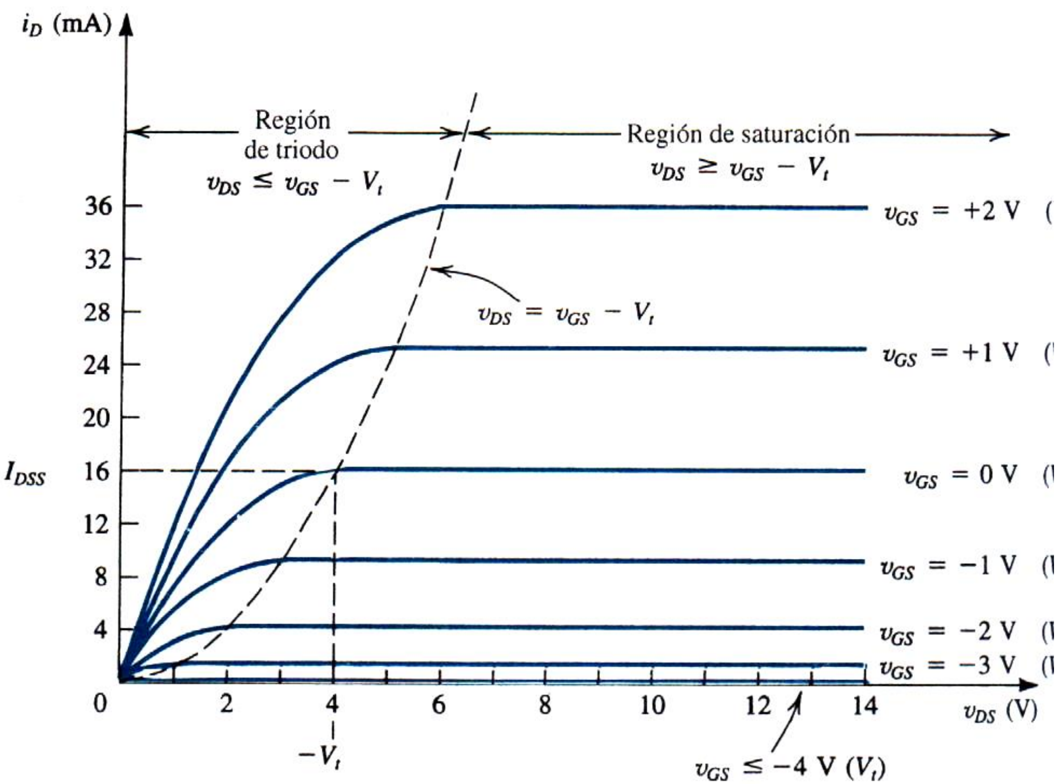
Característica V-I MOS de Enriquecimiento

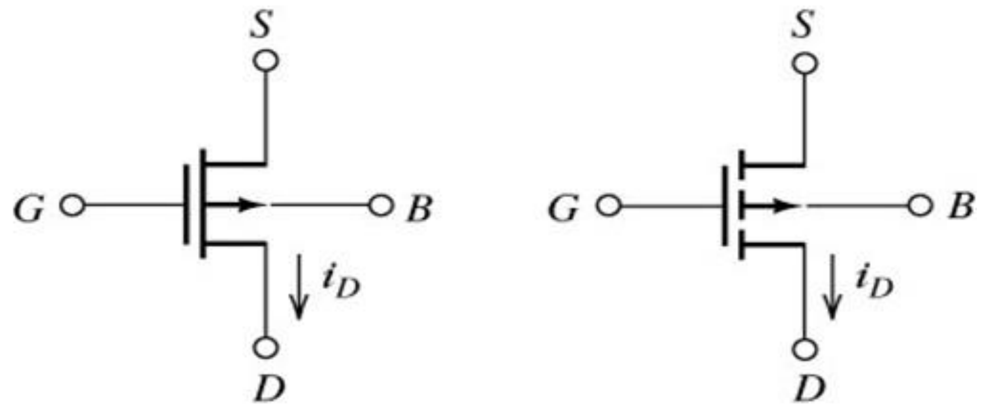




Característica V-I MOS de Deplexión

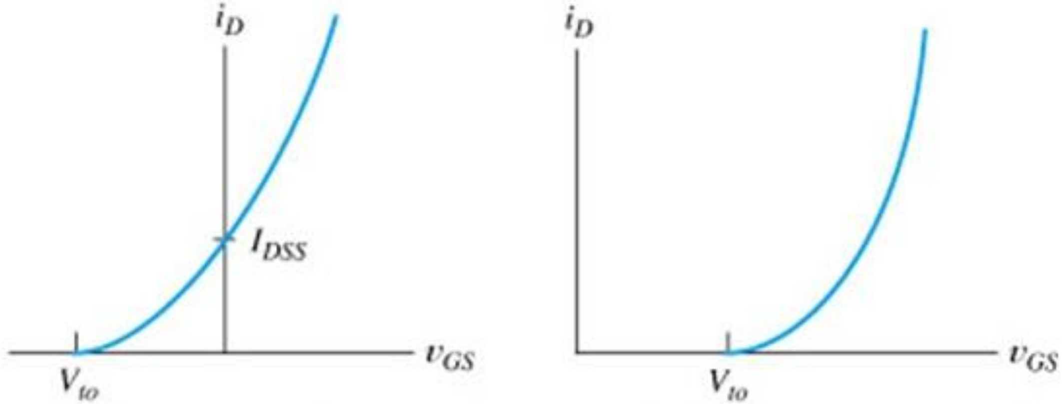






(b) Depletion MOSFET

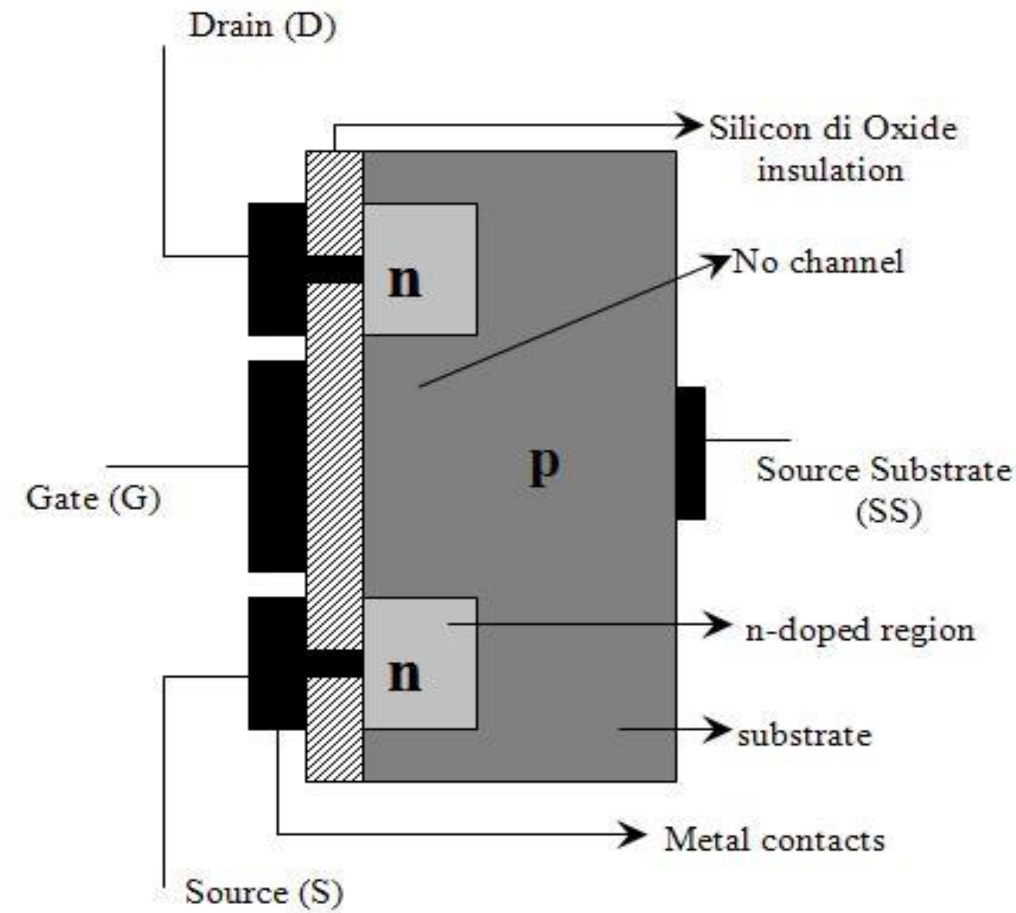
(c) Enhancement MOSFET



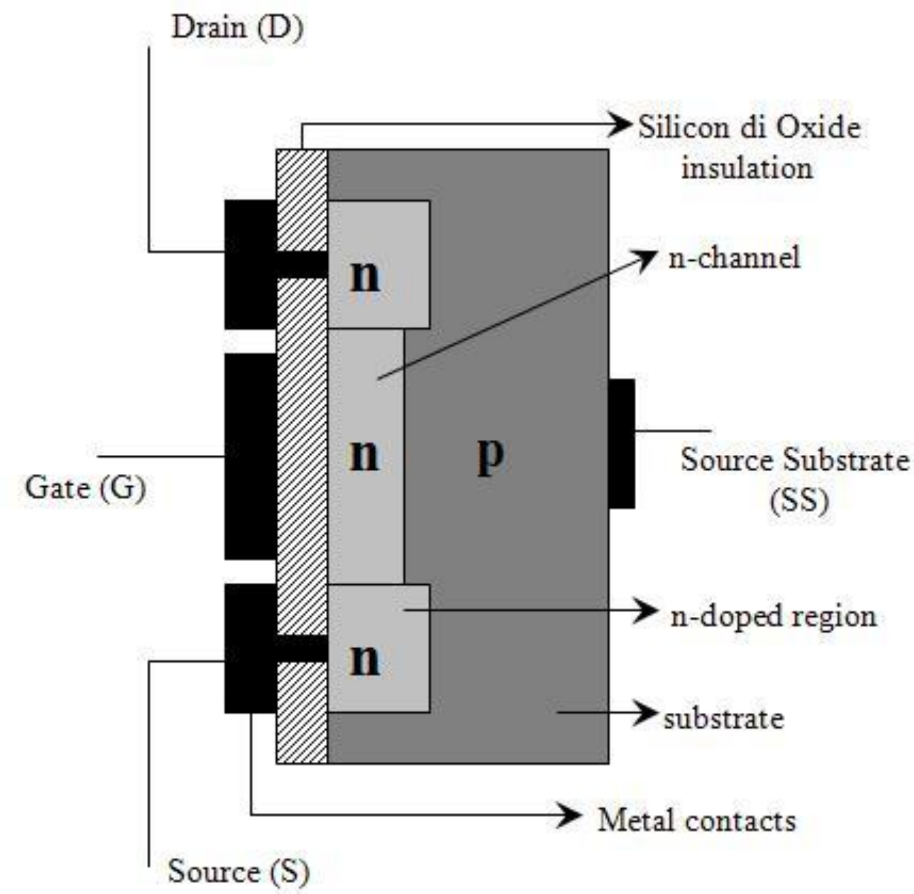
(b) Depletion MOSFET

(c) Enhancement MOSFET

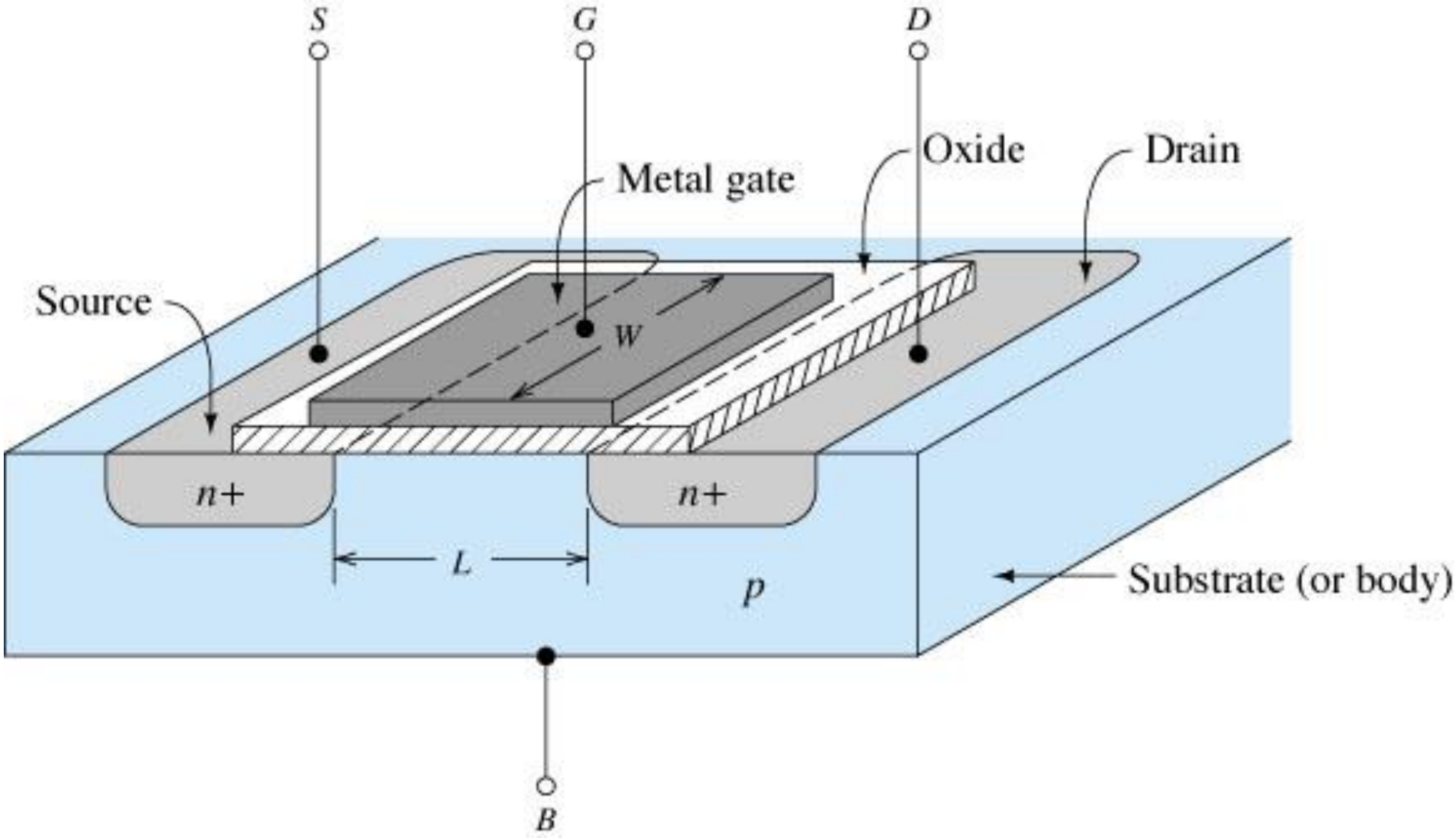
MOS de Enriquecimiento



MOS de Deplexión



Estructura Física



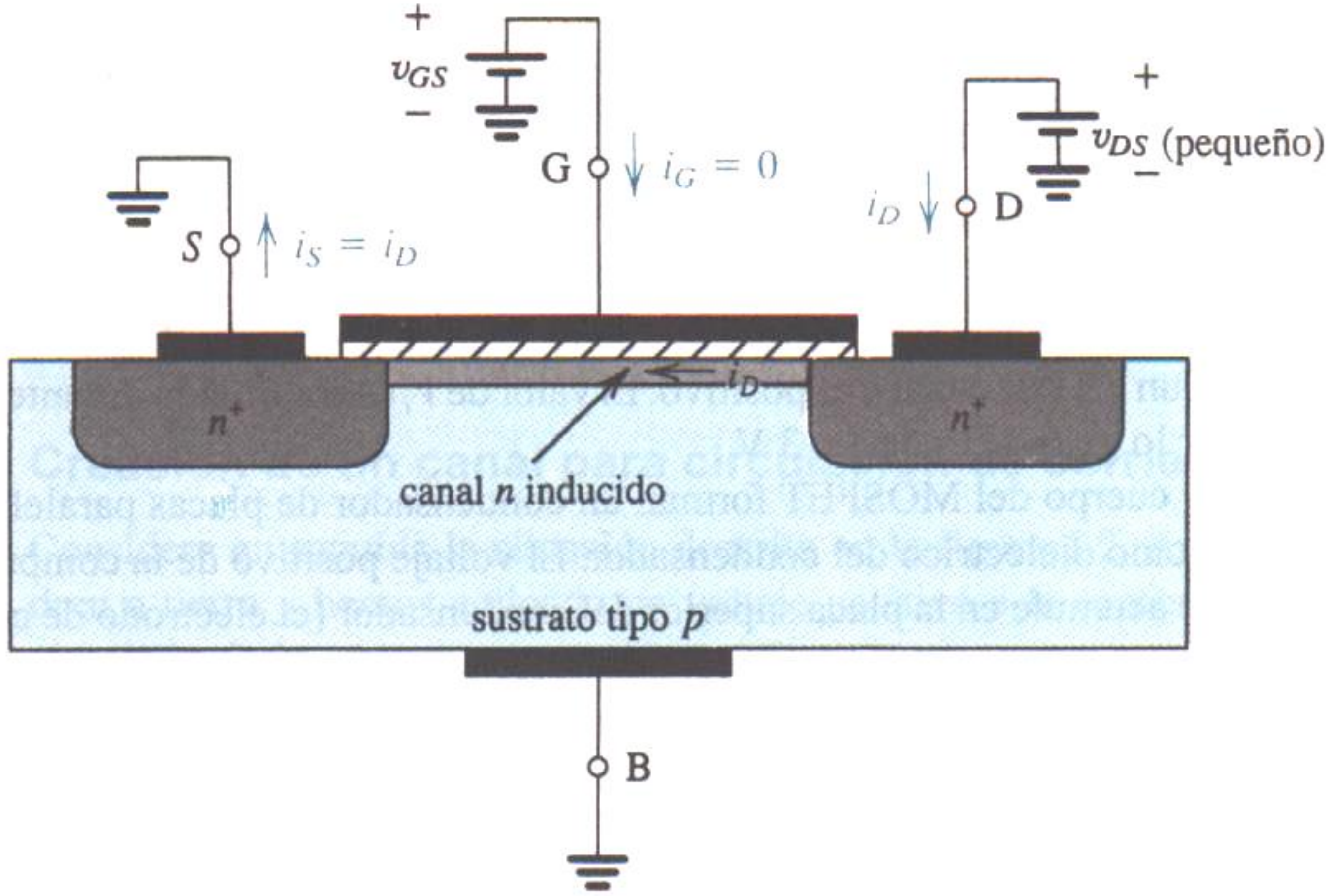
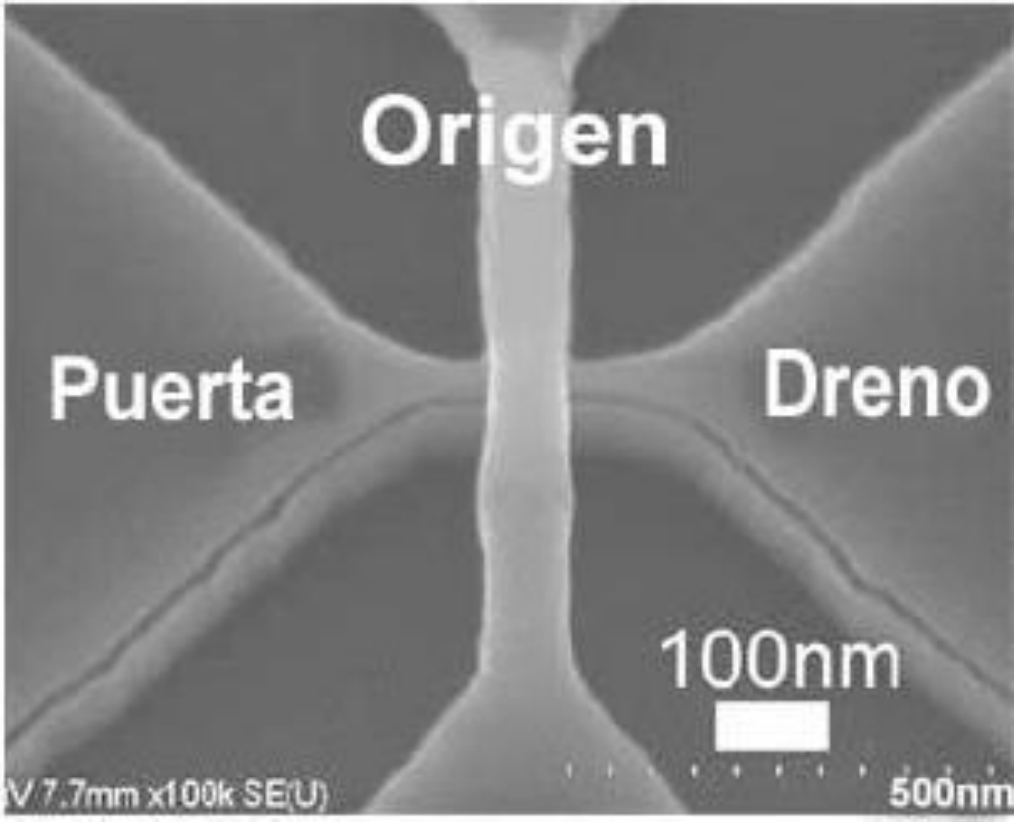
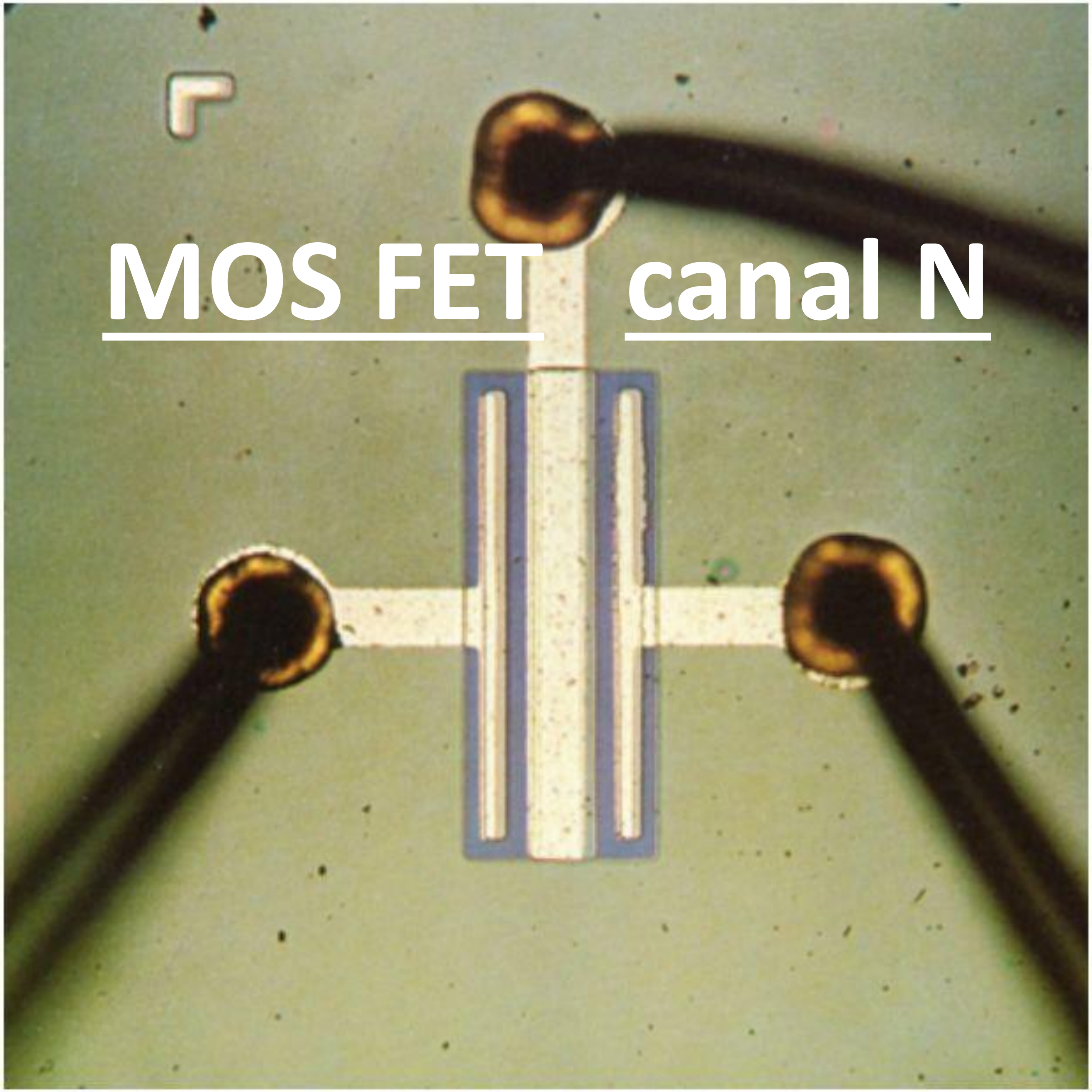

+
v_{GS}
−
G
$i_G = 0$
+
v_{DS} (pequeño)
−
S
$i_S = i_D$
i_D
D
i_D
n^+
n^+
canal *n* inducido
sustrato tipo *p*
B

Imagen de un MOS





Fairchild FI 100 *p*-channel MOS switching transistor.

Credit: Fairchild Camera & Instrument Corporation.

Transistores

- BIPOLARES
  - NPN
  - PNP
- EFECTO DE CAMPO
  - UNIÓN
    - CANAL N (JFET-N)
    - CANAL P (JFET-P)
  - METAL-OXIDO-SEMICONDUCTOR
    - CANAL N (MOSFET-N)
      - ENRIQUECIMIENTO
      - DEPLEXION
    - CANAL P (MOSFET-P)
      - ENRIQUECIMIENTO
      - DEPLEXION

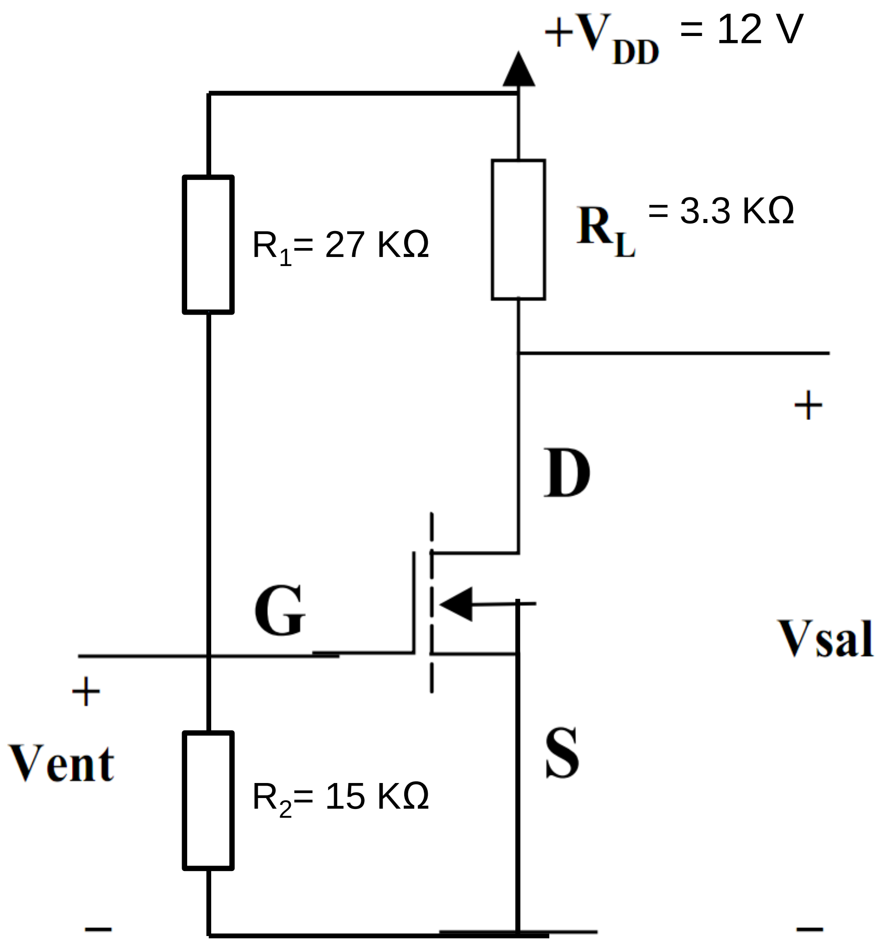
Dr Julius Lilienfield (Alemania) en 1926 patentó el concepto de "*Field Effect Transistor*".

Dr Martín Atalla y Dr Dawon Kahng desarrollaron el primer MOSFET en los laboratorios Bell en 1960

MOSFET

$\beta = 2\ mA/V^2$

$V_{TH} = 2\ V$



$$V_{GS} = \frac{V_{DD} \times R_2}{R_1 + R_2} \qquad V_{GS} = 4{,}28\ V$$

$$V_{Ds} = V_{DD} - I_{DS} \times R_L$$

Que ecuación uso para calcular I_{DS}

1 - Supongo Saturación

$V_{GS} > V_{TH}$ y $V_{GS} – V_{DS} < V_{TH}$

$$I_{DS} = \frac{\beta}{2}(V_{GS} - V_{TH})^2 \qquad I_{DS} = 5{,}2\ mA$$

$$V_{DS} = V_{DD} - I_{DS} \times R_L \qquad V_{DS} = -5{,}2\ V$$

$$V_{GS} - V_{DS} = 9{,}48\ V$$

No verifica la desigualdad $V_{GS} – V_{DS} \nless V_{TH}$

2 - Supongo Óhmico

$V_{GS} > V_{TH}$ y $V_{GS} - V_{DS} > V_{TH}$

$I_{DS}=\beta*(V_{GS}-V_{TH})*V_{DS} - (\beta/2)*V_{DS}^2$ Supongo V_{DS} bajo

$I_{DS}\approx\beta*(V_{GS}-V_{TH})*V_{DS}$ Reemplazo $V_{DS} = V_{DD} - I_{DS} R_L$

$I_{DS}=\beta*(V_{GS}-V_{TH})* (V_{DD} - I_{DS} R_L)$ Resuelvo para I_{DS}

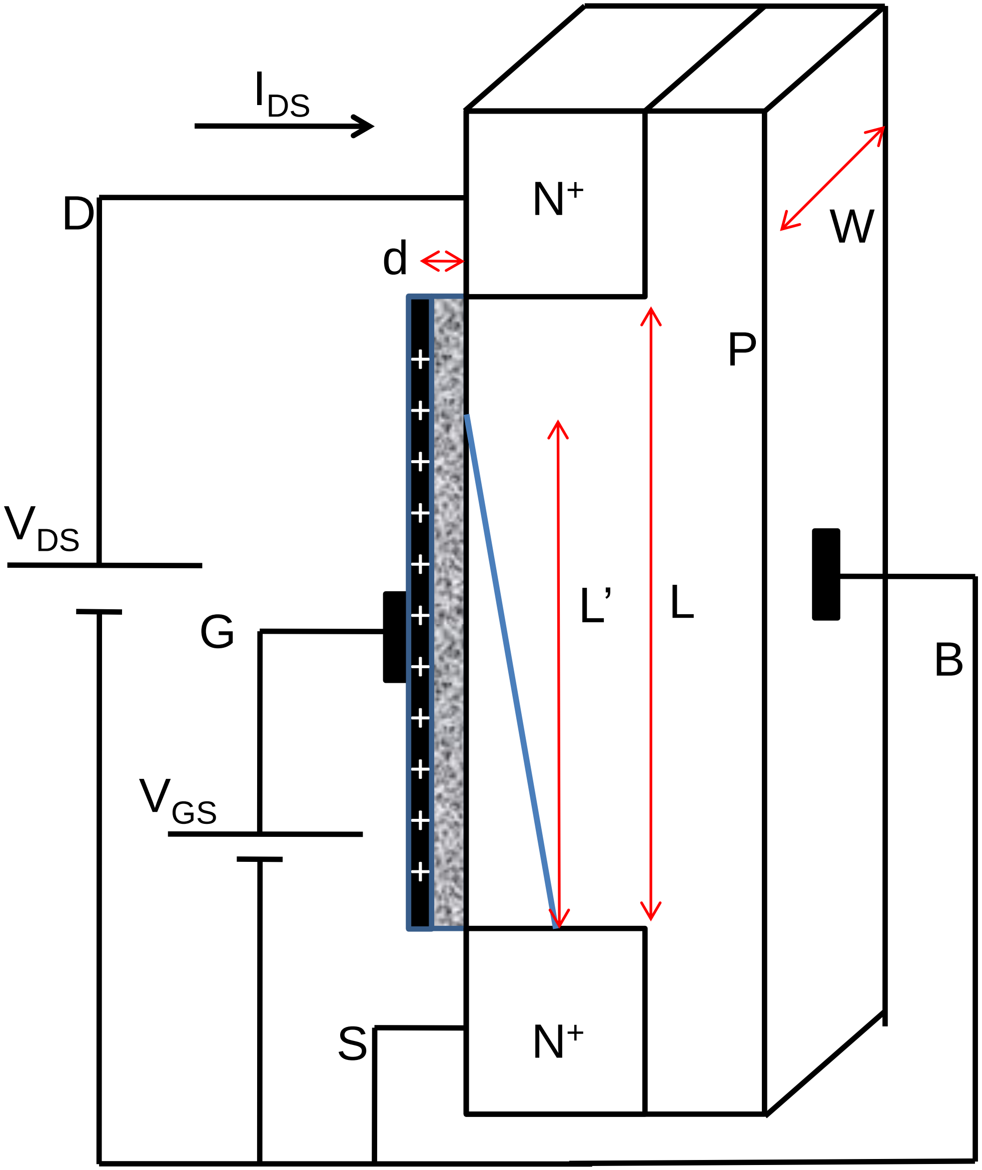
$$I_{DS} = \frac{\beta(V_{GS} - V_{TH})V_{DD}}{1 + \beta(V_{GS} - V_{TH})R_L}$$

$$V_{GS} = 4{,}28\ V$$

$I_{DS} = 3{,}4$ mA $V_{DS} = 0{,}78$ V

Verifico la desigualdad $V_{GS} > V_{TH}$ y $V_{GS} - V_{DS} > V_{TH}$

Como paso a Saturación Aumentando $V_{DS} \rightarrow$ Disminuyo R_L



$$I_{DS} = \frac{\beta}{2}(V_{GS} - V_{TH})^2$$

$$\beta = \frac{\mu\varepsilon}{d}\frac{W}{L} \qquad \beta' = \frac{\mu\varepsilon}{d}\frac{W}{L'}$$

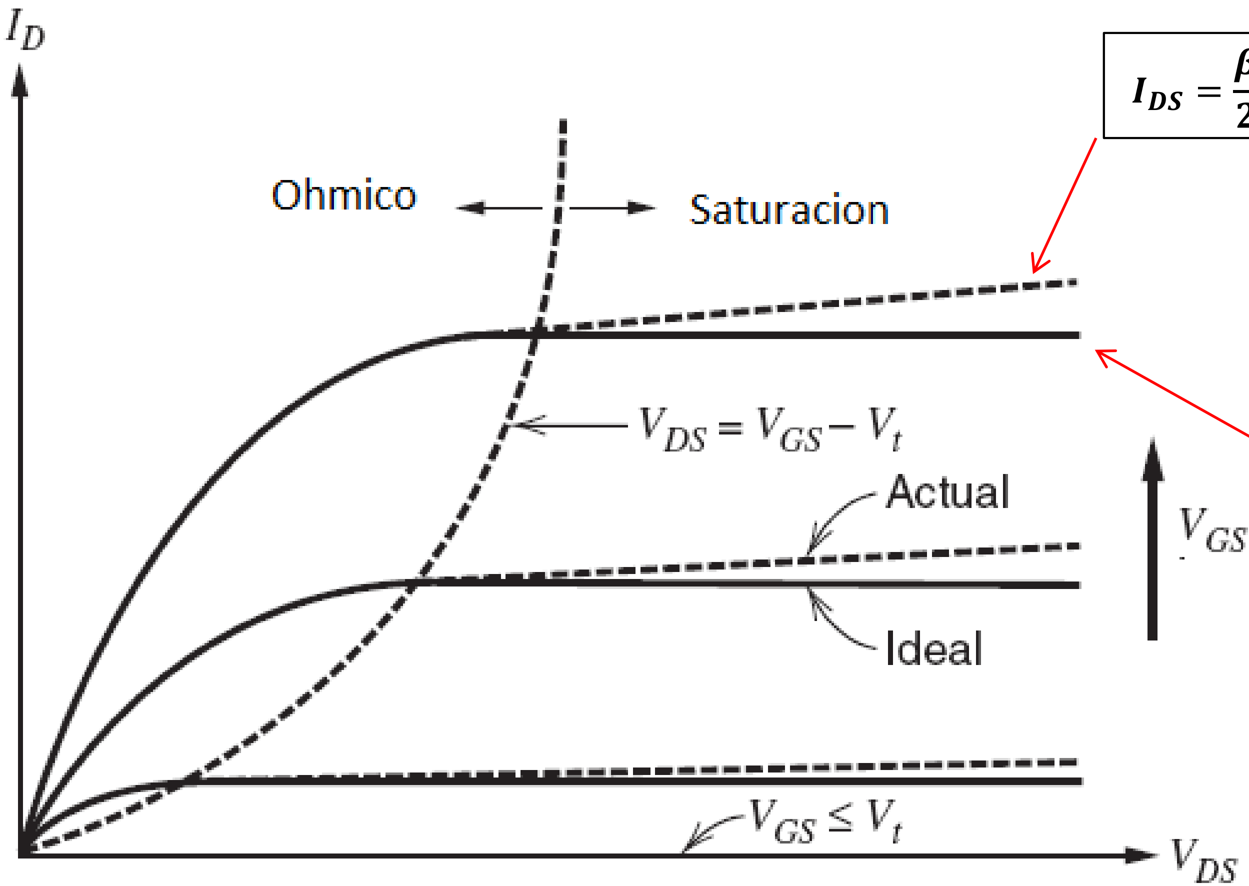
$$\beta \rightarrow f(V_{DS})$$

$$I_{DS} \rightarrow f(V_{DS})$$

$$I_{DS} = \frac{\beta}{2}(1 + \lambda\, V_{DS})(V_{GS} - V_{TH})^2$$

Modulación del largo del canal

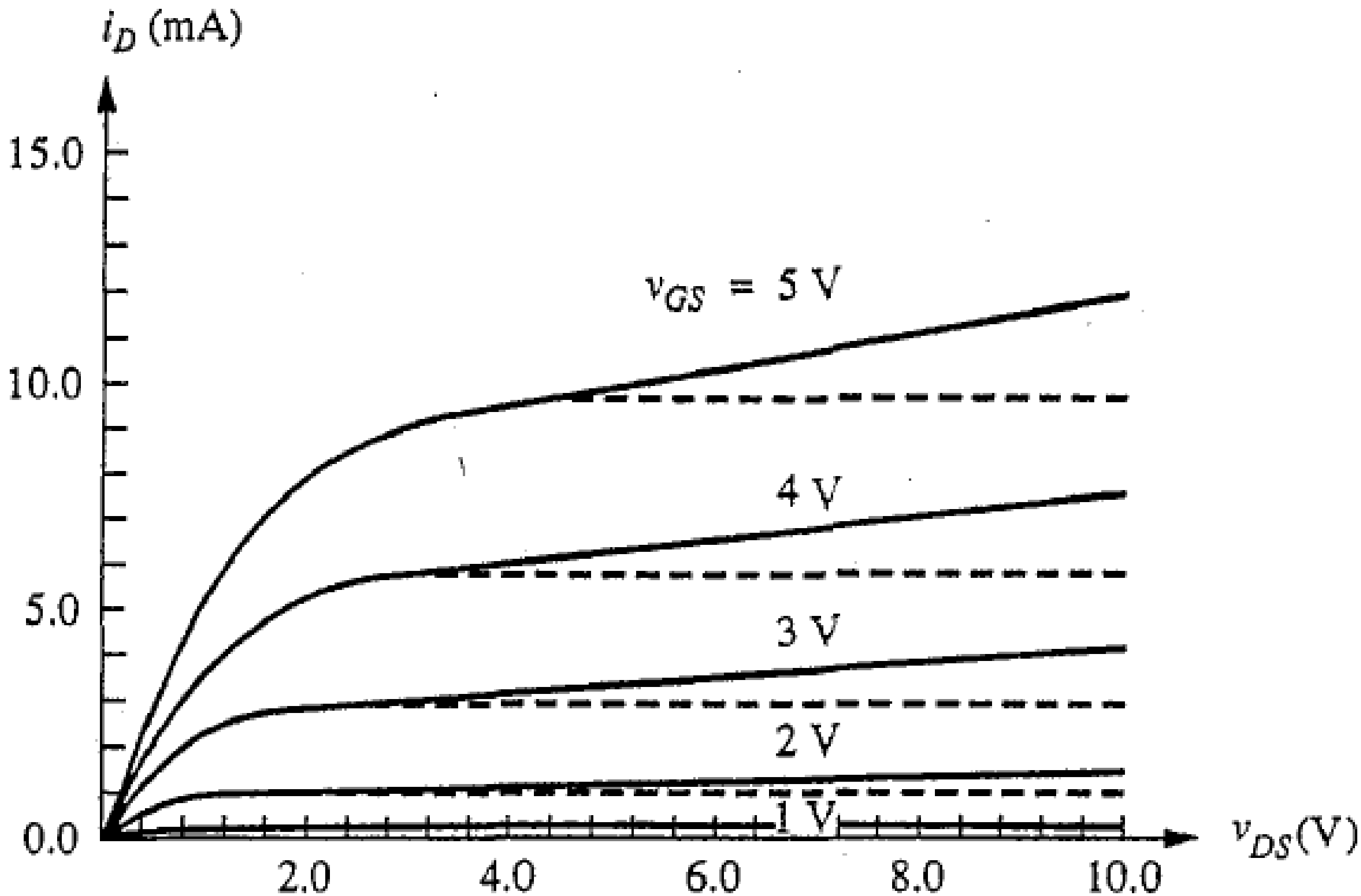
$$I_{DS} = \frac{\beta}{2}(1 + \lambda V_{DS})(V_{GS} - V_{TH})^2$$



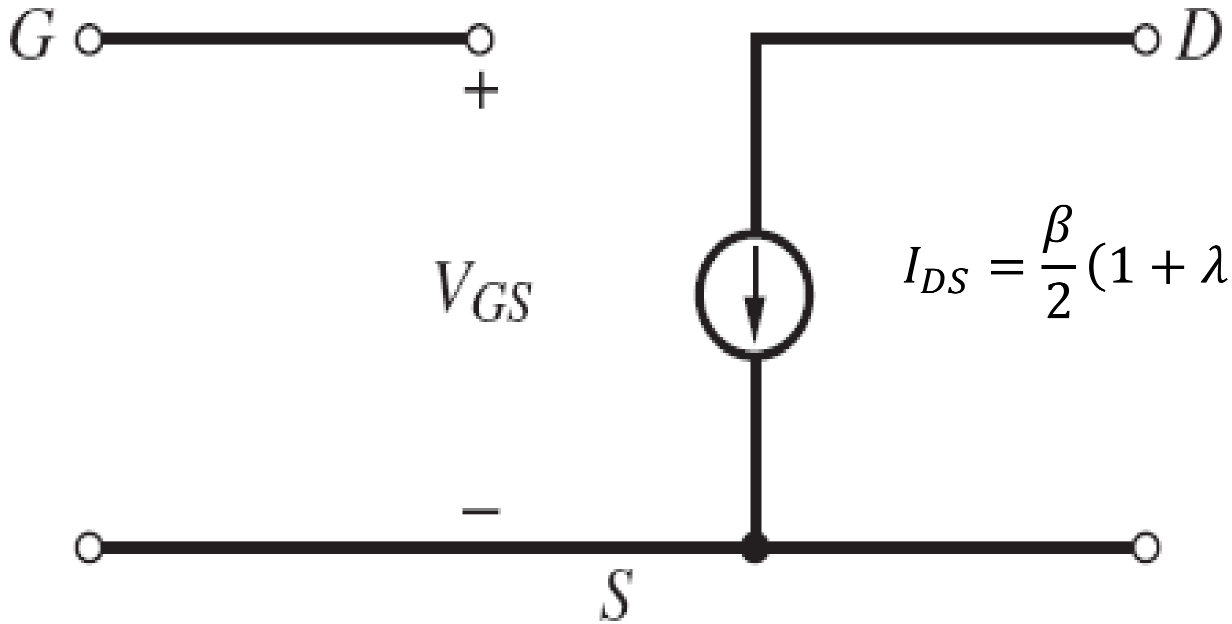
$$I_{DS} = \frac{\beta}{2}(V_{GS} - V_{TH})^2$$

Característica I_{DS} vs V_{DS} del MOSFET

Modulación del largo del canal



Modelo del MOSFET en zona de saturación



$$I_{DS} = \frac{\beta}{2}(1 + \lambda\, V_{DS})(V_{GS} - V_{TH})^2$$